

MAIN CHARACTERISTICS

I_D	160A
V_{DSS}	60V
$R_{DS(on)-typ}$ (@VGS=10V)	2.3mΩ

FEATURES

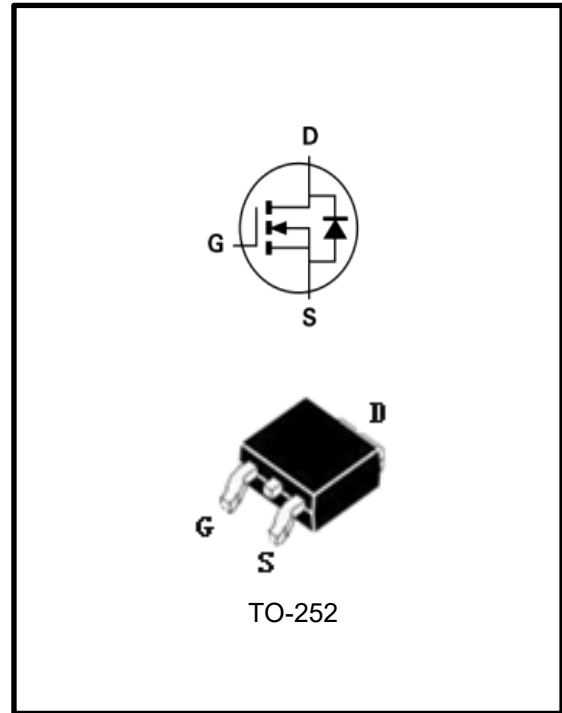
- Fast Switching
- Low ON Resistance
- Low Gate Charge
- 100% Single Pulse avalanche energy Test

APPLICATIONS

- Battery protection
- Load switch
- Uninterruptible power supply

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any



Product specification classification

Part Number	Package	Mode Name	Pack
LG160N06AD	TO-252	LG160N06AD	Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continue Drain Current	I_D	160	A
Pulsed Drain Current (Note1)	I_{DM}	240	A
Power Dissipation	P_D	170	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	650	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.59	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	50	°C/W

Note1:Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

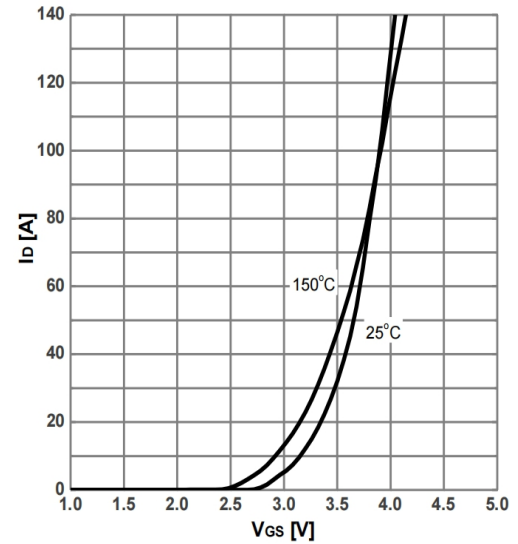
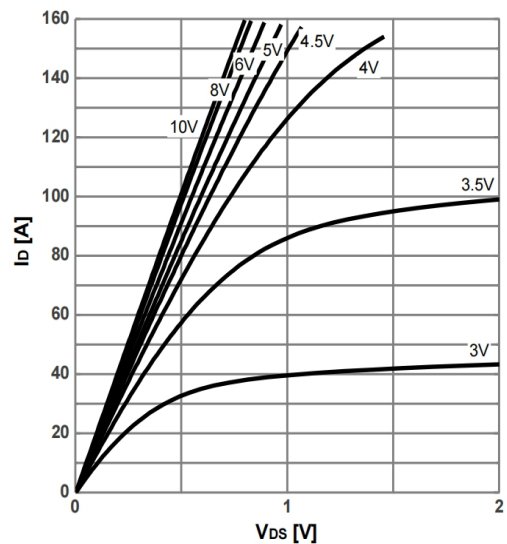
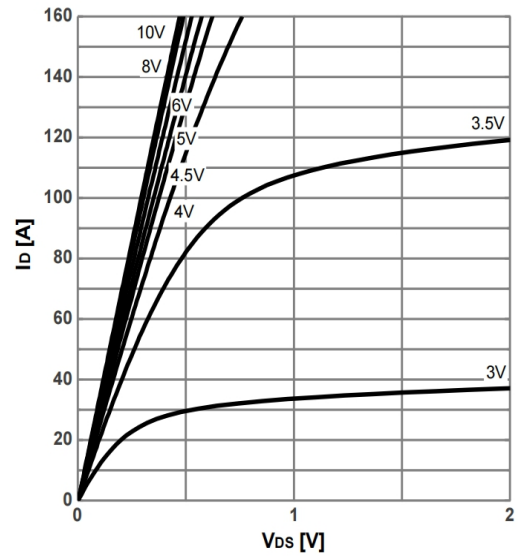
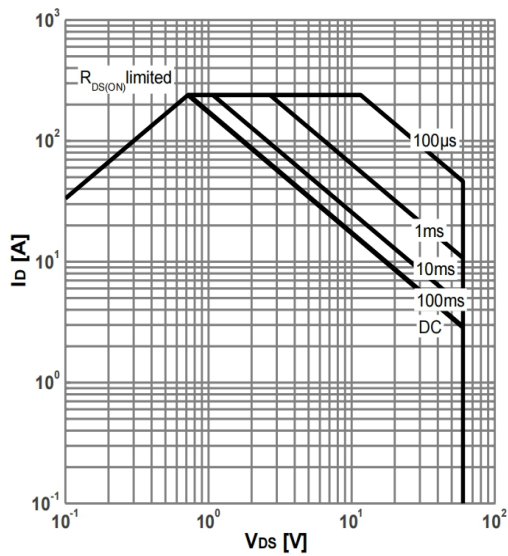
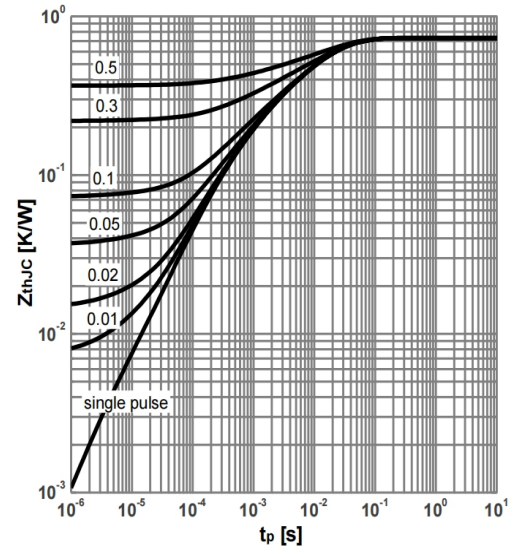
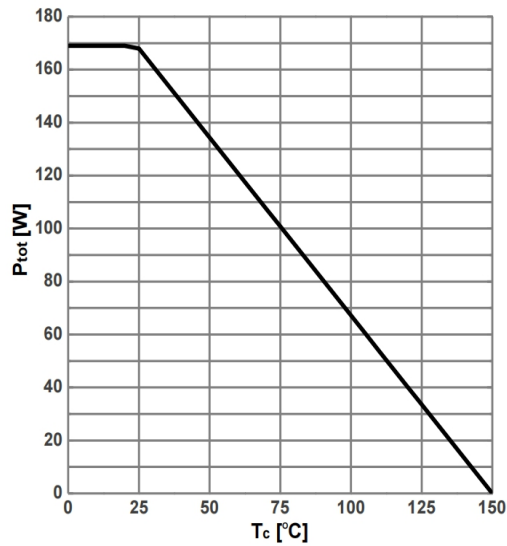
Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	BV_{DSS}	60	-	-	V
Drain-Source Leakage Current	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	$V_{GS(th)}$	2.2	-	3.4	V
Drain-Source On-State Resistance	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	$R_{DS(on)}$	-	2.3	3	m Ω
Transconductance	$V_{DS}=5\text{V}, I_D=20\text{A}$	g_{fs}	-	130	-	S
Input Capacitance	$V_{DS}=25 \text{ V}, V_{GS}=0\text{V}, f=1\text{MHz}$	C_{iss}	-	4200	-	pF
Output Capacitance		C_{oss}	-	1080	-	pF
Reverse Transfer Capacitance		C_{rss}	-	41	-	pF
Turn-on Delay Time(Note2)	$V_{DD}=30 \text{ V}, V_{GS}=10 \text{ V}, R_G=3 \Omega, I_D=100\text{A}$	$t_{d(ON)}$	-	13.5	-	ns
Rise Time(Note2)		t_r	-	95.5	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	40	-	ns
Fall Time(Note2)		t_f	-	110	-	ns
Total Gate Charge(Note2)	$V_{DS}=30\text{V}, V_{GS}=10\text{V}, I_D=20\text{A}$	Q_G	-	42	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	10	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	12	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

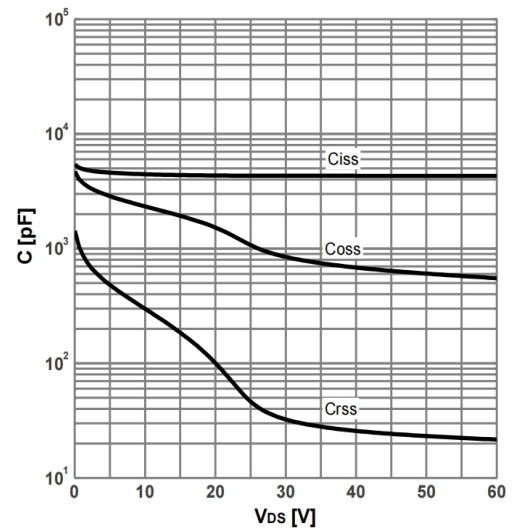
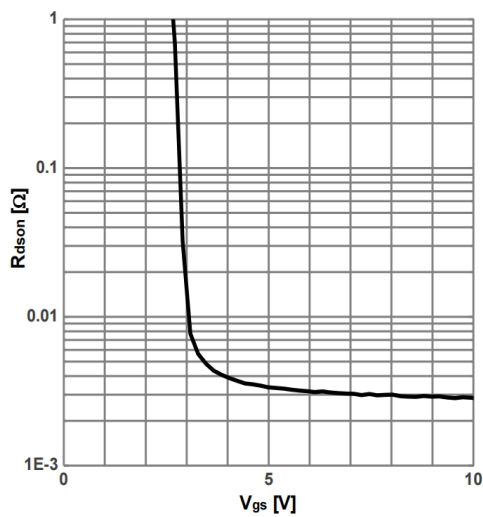
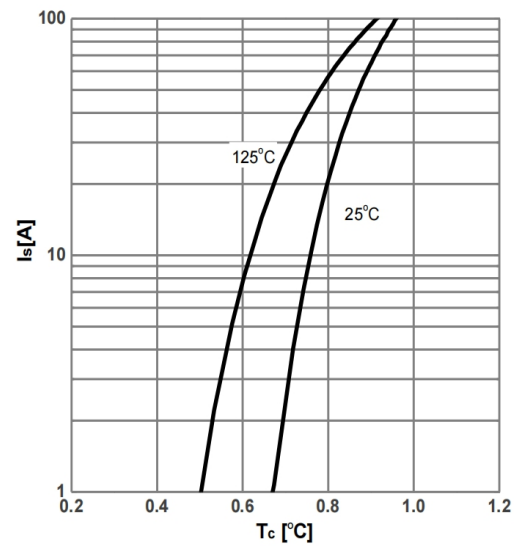
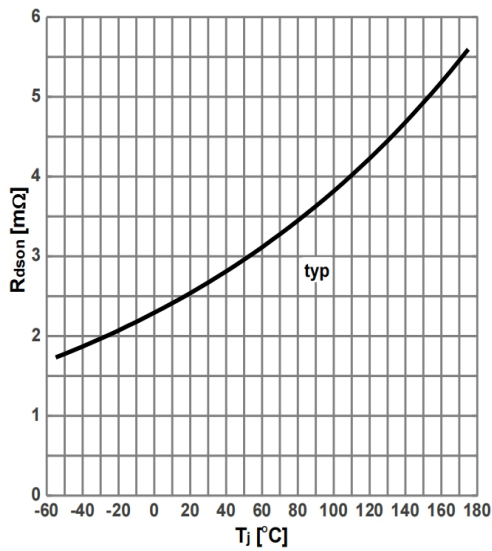
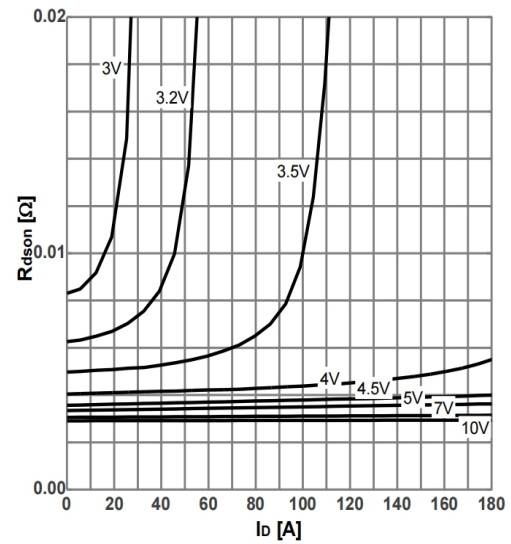
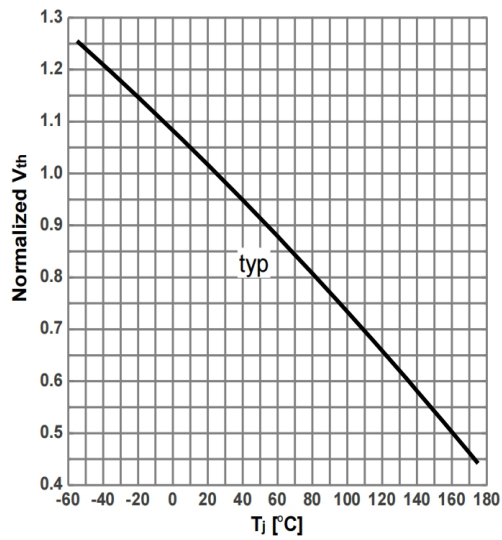
Characteristics	Test Condition	Symbo	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	160	A
Drain-Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_S=20\text{A}, T_J=25^\circ\text{C}$	V_{SD}	-	-	1.2	V
Reverse Recovery Time(Note2)	$T_J = 25^\circ\text{C}, I_F = 60\text{A}$	t_{rr}	-	35	-	ns
Reverse Recovery Charge(Note2)	$di / dt = 100 \text{ A}/\mu\text{s}$	Q_{rr}	-	30	-	nC

Note2:Pulse test: 300 μ s pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

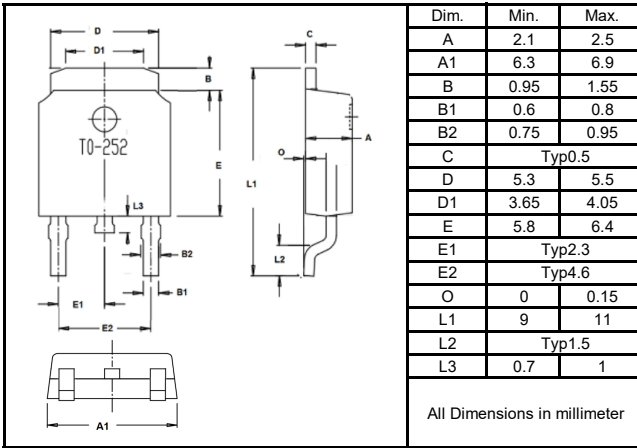


RATINGS AND CHARACTERISTIC CURVES

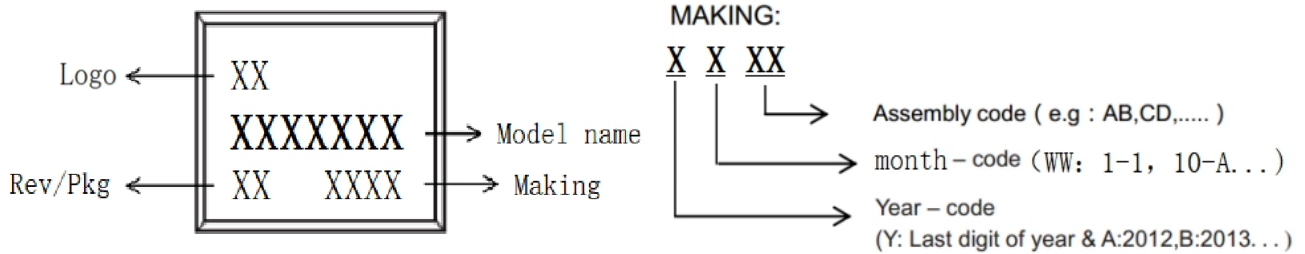


Package Outline Dimensions millimeters

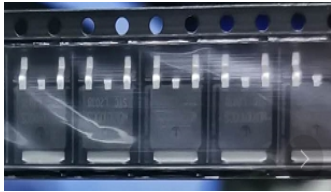
TO-252



Marking on the body



packing instruction

PKG	最小包装	内盒	外箱
TO-252			
	2500pcs/盘	5000pcs/盒	25000pcs/箱

Notice

All product,product specifications and data are subject to change without notice to improve.The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying poer exceeding normal ratedpoer; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this documentpoer; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.